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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	31
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	44-LQFP
Supplier Device Package	44-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100fadfp-50

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RL78/G13 1. OUTLINE

Table 1-1. List of Ordering Part Numbers

(8/12)

Pin count	Package	Data flash	Fields of	Ordering Part Number
			Application Note	
64 pins	64-pin plastic LQFP	Mounted	Α	R5F100LCAFA#V0, R5F100LDAFA#V0,
	(12 × 12 mm, 0.65			R5F100LEAFA#V0, R5F100LFAFA#V0,
	mm pitch)			R5F100LGAFA#V0, R5F100LHAFA#V0,
				R5F100LJAFA#V0, R5F100LKAFA#V0, R5F100LLAFA#V0
				R5F100LCAFA#X0, R5F100LDAFA#X0,
				R5F100LEAFA#X0, R5F100LFAFA#X0,
			D	R5F100LGAFA#X0, R5F100LHAFA#X0,
				R5F100LJAFA#X0, R5F100LKAFA#X0, R5F100LLAFA#X0
				R5F100LCDFA#V0, R5F100LDDFA#V0,
				R5F100LEDFA#V0, R5F100LFDFA#V0,
				R5F100LGDFA#V0, R5F100LHDFA#V0,
				R5F100LJDFA#V0, R5F100LKDFA#V0, R5F100LLDFA#V0
			G	R5F100LCDFA#X0, R5F100LDDFA#X0,
				R5F100LEDFA#X0, R5F100LFDFA#X0,
				R5F100LGDFA#X0, R5F100LHDFA#X0,
				R5F100LJDFA#X0, R5F100LKDFA#X0, R5F100LLDFA#X0
				R5F100LCGFA#V0, R5F100LDGFA#V0,
				R5F100LEGFA#V0, R5F100LFGFA#V0
				R5F100LCGFA#X0, R5F100LDGFA#X0,
				R5F100LEGFA#X0, R5F100LFGFA#X0
				R5F100LGGFA#V0, R5F100LHGFA#V0,
				R5F100LJGFA#V0
				R5F100LGGFA#X0, R5F100LHGFA#X0,
				R5F100LJGFA#X0
		Not	Α	R5F101LCAFA#V0, R5F101LDAFA#V0,
		mounted		R5F101LEAFA#V0, R5F101LFAFA#V0,
				R5F101LGAFA#V0, R5F101LHAFA#V0,
				R5F101LJAFA#V0, R5F101LKAFA#V0, R5F101LLAFA#V0
				R5F101LCAFA#X0, R5F101LDAFA#X0,
				R5F101LEAFA#X0, R5F101LFAFA#X0,
			D	R5F101LGAFA#X0, R5F101LHAFA#X0,
				R5F101LJAFA#X0, R5F101LKAFA#X0, R5F101LLAFA#X0
				R5F101LCDFA#V0, R5F101LDDFA#V0,
				R5F101LEDFA#V0, R5F101LFDFA#V0,
				R5F101LGDFA#V0, R5F101LHDFA#V0,
				R5F101LJDFA#V0, R5F101LKDFA#V0, R5F101LLDFA#V0
				R5F101LCDFA#X0, R5F101LDDFA#X0,
				R5F101LEDFA#X0, R5F101LFDFA#X0,
				R5F101LGDFA#X0, R5F101LHDFA#X0,
				R5F101LJDFA#X0, R5F101LKDFA#X0, R5F101LLDFA#X0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

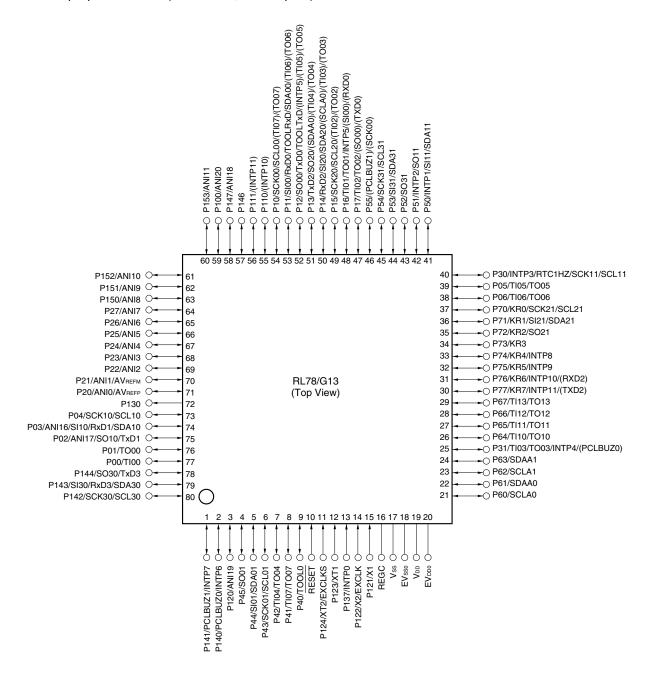
Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



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1.3.12 80-pin products

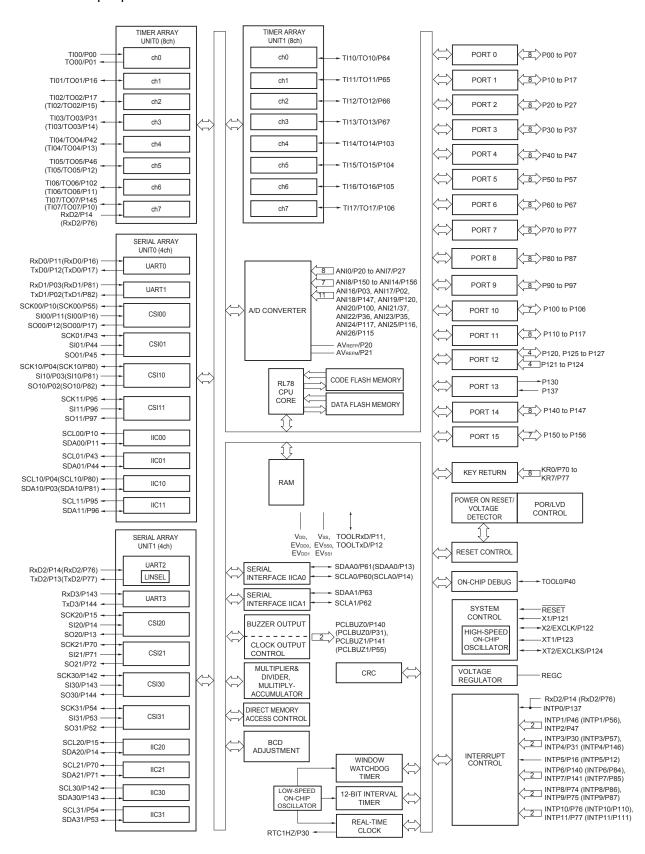
- 80-pin plastic LQFP (14 × 14 mm, 0.65 mm pitch)
- 80-pin plastic LFQFP (12 x 12 mm, 0.5 mm pitch)



- Cautions 1. Make EVsso pin the same potential as Vss pin.
 - 2. Make VDD pin the potential that is higher than EVDDO pin.
 - 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).
- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD} and EV_{DD0} pins and connect the Vss and EV_{SS0} pins to separate ground lines.
 - **3.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register** (**PIOR**) in the RL78/G13 User's Manual.

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1.5.14 128-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

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1.6 Outline of Functions

[20-pin, 24-pin, 25-pin, 30-pin, 32-pin, 36-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

												(1/2)
	Item	20-	pin	24-	pin	25	-pin	30-	pin	32-	pin	36-	pin
		R5F1006x	R5F1016x	R5F1007x	R5F1017x	R5F1008x	R5F1018x	R5F100Ax	R5F101Ax	R5F100Bx	R5F101Bx	R5F100Cx	R5F101Cx
Code flash me	emory (KB)	16 to	o 64	16 t	o 64	16 t	o 64	16 to	128	16 to	128	16 to	128
Data flash me	mory (KB)	4	_	4	-	4	=	4 to 8	=	4 to 8	-	4 to 8	=
RAM (KB)		2 to	4 ^{Note1}	2 to	4 ^{Note1}	2 to	4 ^{Note1}	2 to 1	2 ^{Note1}	2 to ⁻	12 ^{Note1}	2 to 1	2 ^{Note1}
Address space	е	1 MB											
Main system clock	clock HS (High-speed main) mode: 1 to 20 MHz (V _{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)												
	High-speed on-chip oscillator	HS (Hig LS (Lov	High-speed main) mode: 1 to 32 MHz (V_{DD} = 2.7 to 5.5 V), High-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), Low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), Low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)										
Subsystem clo	ock						-	-					
Low-speed on	n-chip oscillator	15 kHz	(TYP.)										
General-purpo	ose registers	(8-bit re	gister ×	8) × 4 ba	nks								
Minimum instr	ruction execution time	0.03125	5 μs (Hig	h-speed	on-chip	oscillato	r: fін = 3	2 MHz op	peration)			
		0.05 μs	(High-s	peed sys	tem cloc	:k: fмx = 1	20 MHz	operatior	۱)				
Instruction set	t	Adde Multip	 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 										
I/O port	Total	1	6	2	0	2	21	2	6	2	8	3	2
	CMOS I/O	1 (N-ch C [Vpp wit voltag	D.D. I/O thstand	(N-ch C	5 D.D. I/O thstand ge]: 6)	(N-ch (5 D.D. I/O thstand ge]: 6)	2 (N-ch C [V _{DD} wit voltag	D.D. I/O thstand	2 (N-ch ([V _{DD} wi voltag	thstand	(N-ch C [V _{DD} with voltage	thstand
	CMOS input	3	3	;	3	;	3	3	3	;	3	3	3
	CMOS output	-	-	-	-		1	_	-	-	-	-	-
	N-ch O.D. I/O (withstand voltage: 6 V)	=	_	2	2	:	2	2	2	(3	3	3
Timer	Timer 16-bit timer 8 channels												
	Watchdog timer						1 cha	annel					
	Real-time clock (RTC)						1 chan	nel Note 2					
	12-bit interval timer (IT)						1 cha	annel					
	Timer output	er output 3 channels (PWM outputs: 3 Note 3) 4 channels (PWM outputs: 3 Note 3) 4 channels (PWM outputs: 3 Note 3) 8 channels (PWM outputs: 7 Note 3) Note 4											
	RTC output						=	=					
· · · · · · · · · · · · · · · · · · ·													

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = 6 to 8, A to C): Start address FF300H R5F100xE, R5F101xE (x = 6 to 8, A to C): Start address FEF00H

For the RAM areas used by the flash library, see Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944).

2. Only the constant-period interrupt function when the low-speed on-chip oscillator clock (fill) is selected

Absolute Maximum Ratings (TA = 25°C) (2/2)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-40	mA
		Total of all pins -170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	-70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	-100	mA
	І ОН2	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
Output current, low	lo _{L1}	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	100	mA
	lo _{L2}	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient	TA	In normal operati	on mode	-40 to +85	°C
temperature		In flash memory	programming mode		
Storage temperature	Tstg			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.2 Oscillator Characteristics

2.2.1 X1, XT1 oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation	Ceramic resonator/	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	1.0		20.0	MHz
frequency (fx) ^{Note}	crystal resonator	$2.4~V \leq V_{DD} < 2.7~V$	1.0		16.0	MHz
		$1.8~V \leq V_{DD} < 2.4~V$	1.0		8.0	MHz
		$1.6~V \leq V_{DD} < 1.8~V$	1.0		4.0	MHz
XT1 clock oscillation frequency (fx) ^{Note}	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to 5.4 System Clock Oscillator.

2.2.2 On-chip oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Oscillators	Parameters		Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	fін			1		32	MHz
High-speed on-chip oscillator		–20 to +85 °C	$1.8~V \leq V_{DD} \leq 5.5~V$	-1.0		+1.0	%
clock frequency accuracy			$1.6~V \leq V_{DD} < 1.8~V$	-5.0		+5.0	%
		–40 to −20 °C	$1.8~V \leq V_{DD} \leq 5.5~V$	-1.5		+1.5	%
			$1.6~V \le V_{DD} < 1.8~V$	-5.5		+5.5	%
Low-speed on-chip oscillator clock frequency	fıL				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H/010C2H) and bits 0 to 2 of HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to AC Characteristics for instruction execution time.

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (4/5)$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V _{OH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iон1 = -10.0 mA	EV _{DD0} –			V
		P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iон1 = -3.0 mA	EV _{DD0} – 0.7			V
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iон1 = -2.0 mA	EV _{DD0} – 0.6			V
			$\label{eq:loss_loss} \begin{array}{l} 1.8 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ \\ I_{\text{OH1}} = -1.5 \ mA \end{array}$	EV _{DD0} – 0.5			٧
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 5.5 \text{ V},$ $I_{\text{OH1}} = -1.0 \text{ mA}$	EV _{DD0} – 0.5			V
	V _{OH2}	P20 to P27, P150 to P156	1.6 V \leq V _{DD} \leq 5.5 V, I _{OH2} = $-100~\mu$ A	V _{DD} - 0.5			V
Output voltage, Vol1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64	$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 20~mA$			1.3	٧	
		to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$\label{eq:loss_loss} \begin{cases} 4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ \\ \text{Iol1} = 8.5 \text{ mA} \end{cases}$			0.7	>
			$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V,$ $I_{\text{OL1}} = 3.0~\text{mA}$			0.6	>
			$2.7~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 1.5~mA$			0.4	V
			$\label{eq:loss_state} \begin{array}{l} 1.8 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ \\ I_{\text{OL1}} = 0.6 \ mA \end{array}$			0.4	V
			$1.6~V \leq EV_{DD0} < 5.5~V,$ $I_{OL1} = 0.3~mA$			0.4	V
	V _{OL2}	P20 to P27, P150 to P156	1.6 V \leq VDD \leq 5.5 V, lol2 = 400 μ A			0.4	V
	Vol3	P60 to P63	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $I_{\text{OL3}} = 15.0 \text{ mA}$			2.0	٧
			$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL3} = 5.0~mA$			0.4	V
			$2.7~\textrm{V} \leq \textrm{EV}_\textrm{DD0} \leq 5.5~\textrm{V},$ $\textrm{Iol3} = 3.0~\textrm{mA}$			0.4	V
			$1.8~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL3} = 2.0~mA$			0.4	V
			$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} < 5.5 \text{ V},$ $\text{Iol3} = 1.0 \text{ mA}$			0.4	V

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

3. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq EV_{DD0} < 4.0 V and 2.3 V \leq V_b \leq 2.7 V

$$\label{eq:maximum transfer rate} \text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \text{ln } (1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.0}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.
- 5. Use it with $EV_{DD0} \ge V_b$.
- **6.** The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 1.8 V \leq EV_{DD0} < 3.3 V and 1.6 V \leq V_b \leq 2.0 V

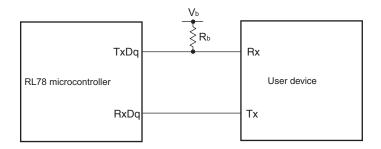
Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times ln \ (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **7.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 6 above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)





(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions	, 0	h-speed Mode	`	/-speed Mode	,	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) Note 1	tsıĸı	$ 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, $	44		110		110		ns
		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
			44		110		110		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$ \begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{array} $	110		110		110		ns
		$C_b = 30$ pF, $R_b = 5.5$ k Ω							
SIp hold time (from SCKp↓) Note 1	t KSI1	$ 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, $	19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$ 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, $	19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$ \begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{array} $	19		19		19		ns
		$C_b = 30$ pF, $R_b = 5.5$ k Ω							
Delay time from SCKp↑ to	tkso1	$ \begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \end{array} $		25		25		25	ns
SOp output Note 1		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$ \begin{array}{c} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \end{array} $		25		25		25	ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$\begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{array}$		25		25		25	ns
		$C_b = 30$ pF, $R_b = 5.5$ k Ω							

Notes

- 1. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 2. Use it with $EV_{DD0} \ge V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (1/2)$

Parameter	Symbol	ĺ	≤ VDD ≤ 5.5 V, Vss =	HS (high- main) ode	LS (low		-	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 1		$4.0 \text{ V} \le \text{EV}_{DD0} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V}$	24 MHz < fмск	14/ fмск		_		_		ns
			20 MHz < fмcκ ≤ 24 MHz	12/ fмск						ns
			8 MHz < fмcк ≤ 20 MHz	10/ fмск		_		_		ns
			4 MHz < fмcк ≤ 8 MHz	8/fмск		16/ fмск		_		ns
			fmck ≤ 4 MHz	6/ƒмск		10/ fмск		10/ fмск		ns
		$2.7 \text{ V} \le \text{EV}_{DD0} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}$	24 MHz < fмск	20/ fмск		_		_		ns
			20 MHz < fмcк ≤ 24 MHz	16/ fмск		_		_		ns
			16 MHz < fмcк ≤ 20 MHz	14/ fмск		_		_		ns
			8 MHz < fмcк ≤ 16 MHz	12/ fмск		_		_		ns
			4 MHz < fмcк ≤ 8 MHz	8/fмск		16/ fмск		_		ns
			fмск ≤ 4 MHz	6/ƒмск		10/ fмск		10/ fмск		ns
		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}^{\text{Note}}$	24 MHz < fмск	48/ fмск		_		_		ns
		2	20 MHz < fмcк ≤ 24 MHz	36/ fмск		_		_		ns
			16 MHz < fмcк ≤ 20 MHz	32/ fмск		_		_		ns
			8 MHz < f _{MCK} ≤ 16 MHz	26/ fмск						ns
		4	4 MHz < f _{MCK} ≤ 8 MHz	16/ fмск		16/ fмск		_		ns
			fмcк ≤ 4 MHz	10/ fмск		10/ fмск		10/ fмск		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)

(2) I2C fast mode

(Ta = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Сог	nditions	, ,	h-speed Mode	`	/-speed Mode	LV (low-voltage main) Mode		Unit
					MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode:	$2.7~V \le EV_{DD0} \le 5.5~V$	0	400	0	400	0	400	kHz
		fc∟κ≥ 3.5 MHz	1.8 V ≤ EV _{DD0} ≤ 5.5 V	0	400	0	400	0	400	kHz
Setup time of restart	tsu:sta	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	0.6		0.6		0.6		μS
condition		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	0.6		0.6		0.6		μS
Hold time ^{Note 1}	thd:sta	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	0.6		0.6		0.6		μS
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	0.6		0.6		0.6		μS
Hold time when SCLA0 =	tLOW	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	1.3		1.3		1.3		μS
" <u>L</u> "		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	1.3		1.3		1.3		μS	
Hold time when SCLA0 =	t HIGH	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	0.6		0.6		0.6		μS
"H"		$1.8~V \leq EV_{DD0} \leq 5.5~V$		0.6		0.6		0.6		μS
Data setup time	tsu:dat	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	100		100		100		μS
(reception)		1.8 V ≤ EV _{DD0} ≤ 5.8	5 V	100		100		100		μS
Data hold time	thd:dat	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	0	0.9	0	0.9	0	0.9	μS
(transmission)Note 2		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.8$	5 V	0	0.9	0	0.9	0	0.9	μS
Setup time of stop	tsu:sto	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.$	2.7 V ≤ EV _{DD0} ≤ 5.5 V			0.6		0.6		μS
condition		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.$	1.8 V ≤ EV _{DD0} ≤ 5.5 V			0.6		0.6		μS
Bus-free time	t BUF	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.8$	2.7 V ≤ EV _{DD0} ≤ 5.5 V			1.3		1.3		μS
		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.8$	5 V	1.3		1.3		1.3		μS

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IoH1, IoL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

<R>

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI0, ANI2 to ANI14, ANI16 to ANI26

(Ta = -40 to +85°C, 2.4 V \leq VDD \leq 5.5 V, 1.6 V \leq EVDD0 = EVDD1 \leq VDD, Vss = EVss0 = EVss1 = 0 V, Reference voltage (+) = VBGR Note 3, Reference voltage (-) = AVREFM = 0 V Note 4, HS (high-speed main) mode)

Parameter	Symbol	Cond	itions	MIN.	TYP.	MAX.	Unit
Resolution	RES				8		bit
Conversion time	tconv	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
Integral linearity errorNote 1	ILE	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±1.0	LSB
Analog input voltage	VAIN			0		V _{BGR} Note 3	V

- Notes 1. Excludes quantization error (±1/2 LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - 3. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.
 - 4. When reference voltage (-) = Vss, the MAX. values are as follows.
 Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM.
 Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.
 Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.

2.8 Flash Memory Programming Characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fclk	$1.8~V \leq V \text{dd} \leq 5.5~V$	1		32	MHz
Number of code flash rewrites	Cerwr	Retained for 20 years TA = 85°C	1,000			Times
Number of data flash rewrites		Retained for 1 years TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°C	100,000			
		Retained for 20 years TA = 85°C	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite.

- The retaining years are until next rewrite after the rewrite.
- 2. When using flash memory programmer and Renesas Electronics self programming library
- **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

Remark The electrical characteristics of the products G: Industrial applications (T_A = -40 to +105°C) are different from those of the products "A: Consumer applications, and D: Industrial applications". For details, refer to **3.1** to **3.10**.

3.1 Absolute Maximum Ratings

Absolute Maximum Ratings ($T_A = 25$ °C) (1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V _{DD}		-0.5 to +6.5	٧
	EV _{DD0} , EV _{DD1}	EV _{DD0} = EV _{DD1}	-0.5 to +6.5	V
	EVsso, EVss1	EVsso = EVss1	-0.5 to +0.3	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8 and $-0.3 \text{ to V}_{DD} +0.3^{\text{Note 1}}$	V
Input voltage	VII	P00 to P07, P10 to P17, P30 to P37, P40 to P47,	-0.3 to EV _{DD0} +0.3	V
		P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	and -0.3 to V _{DD} +0.3 ^{Note 2}	
	V _{I2}	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	Vı3	P20 to P27, P121 to P124, P137, P150 to P156, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Output voltage	V ₀₁	P00 to P07, P10 to P17, P30 to P37, P40 to P47,	-0.3 to EV _{DD0} +0.3	٧
		P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	and –0.3 to V _{DD} +0.3 ^{Note 2}	
	V _{O2}	P20 to P27, P150 to P156	-0.3 to V _{DD} +0.3 Note 2	٧
Analog input voltage	VAI1	ANI16 to ANI26	-0.3 to EV _{DD0} +0.3 and -0.3 to AV _{REF} (+) +0.3 $^{\text{Notes 2, 3}}$	V
	V _{Al2}	ANI0 to ANI14	-0.3 to V _{DD} +0.3 and -0.3 to AV _{REF} (+) +0.3 $^{\text{Notes 2, 3}}$	V

- **Notes 1.** Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 2. Must be 6.5 V or lower.
 - 3. Do not exceed AVREF(+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - **2.** $AV_{REF}(+)$: + side reference voltage of the A/D converter.
 - 3. Vss : Reference voltage



 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (2/5)$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low ^{Note 1}		Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147				8.5 Note 2	mA
		Per pin for P60 to P63				15.0 Note 2	mA
		Total of P00 to P04, P07, P32 to	$4.0~V \leq EV_{DD0} \leq 5.5~V$			40.0	mA
			$2.7~V \leq EV_{DD0} < 4.0~V$			15.0	mA
	P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145 (When duty ≤ 70% Note 3)	$2.4~\text{V} \leq \text{EV}_{\text{DD0}} < 2.7~\text{V}$			9.0	mA	
	Total of P05, P06, P10 to P17, P30,	$4.0~V \leq EV_{DD0} \leq 5.5~V$			40.0	mA	
			$2.7~V \leq EV_{DD0} < 4.0~V$			35.0	mA
		P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147 $(\text{When duty} \leq 70\%^{\text{Note 3}})$	2,4 V ≤ EV _{DD0} < 2.7 V			20.0	mA
	Total of all pins (When duty ≤ 70% Note 3)				80.0	mA	
	lo _{L2}	Per pin for P20 to P27, P150 to P156			_	0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	$2.4~V \leq V_{DD} \leq 5.5~V$			5.0	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso, EVss1 and Vss pin.
 - 2. Do not exceed the total current value.
 - **3.** Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(lol \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and IoL = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7 \text{ mA}$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

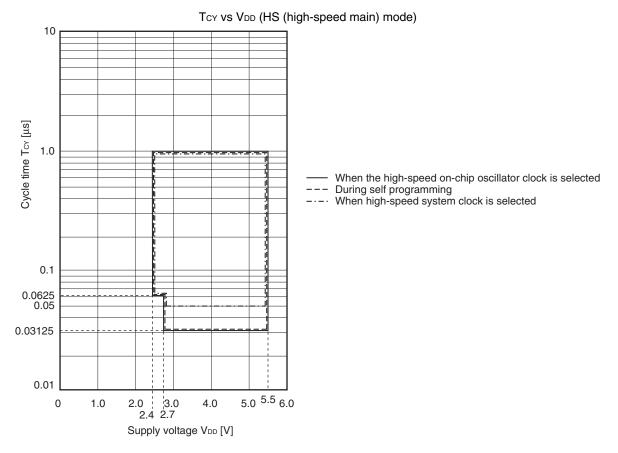
Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (5/5)$

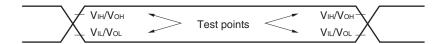
Items	Symbol	Conditio	ns		MIN.	TYP.	MAX.	Unit
Input leakage current, high	Ілн1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	VI = EVDD0				1	μΑ
	ILIH2	P20 to P27, P137, P150 to P156, RESET	$V_I = V_{DD}$				1	μΑ
	Ішнз	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = VDD	In input port or external clock input			1	μΑ
				In resonator connection			10	μΑ
Input leakage current, low	1ш1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Vı = EVsso				-1	μΑ
	ILIL2	P20 to P27, P137, P150 to P156, RESET	Vı = Vss				-1	μΑ
	ILIL3	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	Vı = Vss	In input port or external clock input			-1	μΑ
				In resonator connection			-10	μΑ
On-chip pll-up resistance	Ru	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	V _I = EVsso	, In input port	10	20	100	kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

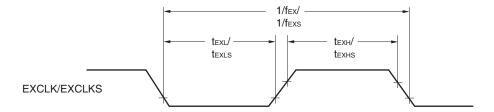
Minimum Instruction Execution Time during Main System Clock Operation



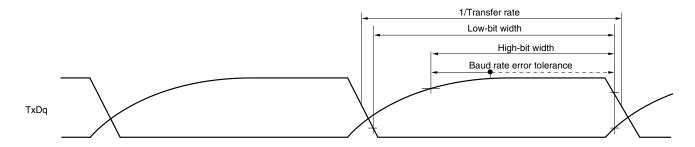
AC Timing Test Points

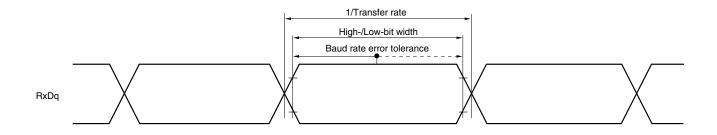


External System Clock Timing



UART mode bit width (during communication at different potential) (reference)





- $\begin{tabular}{ll} \textbf{Remarks 1.} & R_b[\Omega]: Communication line (TxDq) pull-up resistance, \\ & C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage \\ \end{tabular}$
 - **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))
 - **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode) (1/2) (T_A = -40 to +105°C, 2.4 V \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 V, Vss = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-s	Unit		
			MIN.	MAX.		
SCLr clock frequency	fscL	$\begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$		400 Note 1	kHz	
		$\begin{aligned} 2.7 \ V &\leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$		400 Note 1	kHz	
		$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $		100 Note 1	kHz	
		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega$		100 Note 1	kHz	
		$\begin{aligned} &2.4 \; V \leq EV_{DD0} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{aligned}$		100 Note 1	kHz	
Hold time when SCLr = "L"	tLOW	$\begin{aligned} 4.0 & \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 & \ V \leq V_b \leq 4.0 \ V, \\ C_b = 50 & \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$	1200		ns	
		$\begin{split} & 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$	1200		ns	
		$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $	4600		ns	
		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega$	4600		ns	
		$2.4 \ V \leq EV_{DD0} < 3.3 \ V,$ $1.6 \ V \leq V_b \leq 2.0 \ V,$ $C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega$	4650		ns	
Hold time when SCLr = "H"	tнівн	$\begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$	620		ns	
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega$	500		ns	
		$\begin{aligned} &4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ &2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.8 \text{ k}\Omega \end{aligned}$	2700		ns	
		$\begin{split} 2.7 \ V &\leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 100 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	2400		ns	
		$2.4 \ V \leq EV_{DD0} < 3.3 \ V,$ $1.6 \ V \leq V_b \leq 2.0 \ V,$ $C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega$	1830		ns	

(${f Notes}$ and ${f Caution}$ are listed on the next page, and ${f Remarks}$ are listed on the page after the next page.)

4.11 64-pin Products

R5F100LCAFA, R5F100LDAFA, R5F100LEAFA, R5F100LFAFA, R5F100LGAFA, R5F100LHAFA, R5F100LJAFA, R5F100LKAFA, R5F100LLAFA

R5F101LCAFA, R5F101LDAFA, R5F101LEAFA, R5F101LFAFA, R5F101LGAFA, R5F101LHAFA, R5F101LJAFA, R5F101LKAFA, R5F101LLAFA

R5F100LCDFA, R5F100LDDFA, R5F100LEDFA, R5F100LFDFA, R5F100LGDFA, R5F100LHDFA, R5F100LJDFA, R5F100LKDFA, R5F100LLDFA

R5F101LCDFA, R5F101LDDFA, R5F101LEDFA, R5F101LFDFA, R5F101LGDFA, R5F101LHDFA, R5F101LJDFA, R5F101LKDFA, R5F101LLDFA

Previous Code

MASS (TYP.) [g]

R5F100LCGFA, R5F100LDGFA, R5F100LEGFA, R5F100LFGFA, R5F100LGGFA, R5F100LHGFA, R5F100LJGFA

RENESAS Code

JEITA Package Code

